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**FERROELECTRIC MEMORY DEVICE AND
METHOD OF FORMING THE SAME**

ABSTRACT OF THE DISCLOSURE

5 A ferroelectric memory device along with a method of forming the same are provided.
A first interlayer insulating layer is formed on a semiconductor substrate. A buried contact
structure is formed on the first interlayer insulating layer. The buried contact structure is
electrically connected to the substrate through a first contact hole extending through the first
10 interlayer insulating layer. A blocking layer covers or encapsulates the buried contact
structure and the first interlayer insulating layer. A second interlayer insulating layer is
formed on the blocking layer. A ferroelectric capacitor formed on the second interlayer
insulating layer and is electrically connected to the buried contact structure through a second
contact hole that penetrates the second interlayer insulating layer and the blocking layer.